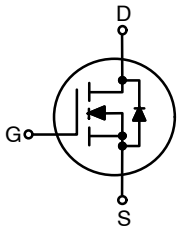
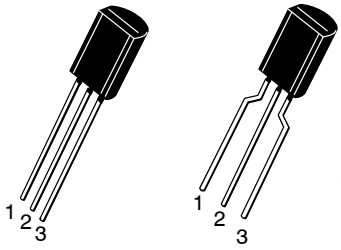
N-Channel Enhancement Mode Field Effect Transistor

2N7000, 2N7002, NDS7002A





TO–92
CASE 135AN

TO–92
CASE 135AR

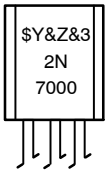
Description

These N−channel enhancement mode field effect transistors are produced using **onsemi**'s proprietary, high cell density, DMOS technology. These products have been designed to minimize on−state resistance while providing rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 400 mAdc and can deliver pulsed currents up to 2 A. These products are particularly suited for low−voltage, low−current applications, such as small servo motor control, power MOSFET gate drivers, and other switching applications.

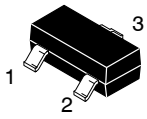
Features

- High Density Cell Design for Low $R_{DS(on)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- High Saturation Current Capability
- This Device is Pb−Free and Halogen Free

MARKING DIAGRAM

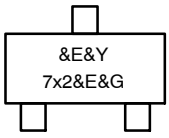


$Y = Logo
&Z = Assembly Plant Code
&3 = Date Code
2N7000 = Specific Device Code



SOT−23
CASE 318−08

MARKING DIAGRAM



&E = Designates Space
&Y = Binary Calendar Year Coding Scheme
7x2 = Specific Device Code
x= 0, 1
&G = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

ABSOLUTE MAXIMUM RATINGS Values are at T_C = 25°C unless otherwise noted.

Symbol	Parameter	Value			Unit
		2N7000	2N7002	NDS7002A	
V_{DSS}	Drain−to−Source Voltage	60			V
V_{DGR}	Drain−Gate Voltage (R_{GS} ≤ 1 MW)	60			V
V_{GSS}	Gate−Source Voltage − Continuous	±20			V
	Gate−Source Voltage − Non Repetitive (tp < 50 ms)	±40			
I_D	Maximum Drain Current − Continuous	200	115	280	mA
	Maximum Drain Current − Pulsed	500	800	1500	
P_D	Maximum Power Dissipation Derated above 25°C	400	200	300	mW
		3.2	1.6	2.4	mW/°C
T_J, T_{STG}	Operating and Storage Temperature Range	−55 to 150		−65 to 150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/16−inch from Case for 10 s	300			°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS Values are at T_C = 25°C unless otherwise noted.

Symbol	Parameter	Value			Unit
		2N7000	2N7002	NDS7002A	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	312.5	625	417	°C/W

ELECTRICAL CHARACTERISTICS
Values are at T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Type	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS							
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 10 μA	All	60	–	–	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 48 V, V_{GS} = 0 V	2N7000	–	–	1	μA
		V_{DS} = 48 V, V_{GS} = 0 V, T_C = 125°C		–	–	1	mA
		V_{DS} = 60 V, V_{GS} = 0 V	2N7002 NDS7002A	–	–	1	μA
		V_{DS} = 60 V, V_{GS} = 0 V, T_C = 125°C		–	–	0.5	mA
I_{GSSF}	Gate − Body Leakage, Forward	V_{GS} = 15 V, V_{DS} = 0 V	2N7000	–	–	10	nA
		V_{GS} = 20 V, V_{DS} = 0 V	2N7002 NDS7002A	–	–	100	
I_{GSSR}	Gate − Body Leakage, Reverse	V_{GS} = −15 V, V_{DS} = 0 V	2N7000	–	–	−10	nA
		V_{GS} = −20 V, V_{DS} = 0 V	2N7002 NDS7002A	–	–	−100	
ON CHARACTERISTICS							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 1 mA	2N7000	0.8	2.1	3	V
		V_{DS} = V_{GS}, I_D = 250 μA	2N7002 NDS7002A	1	2.1	2.5	

ELECTRICAL CHARACTERISTICS (continued)
Values are at T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Type	Min.	Typ.	Max.	Unit
ON CHARACTERISTICS							
$R_{DS(on)}$	Static Drain−Source On−Resistance	V_{GS} = 10 V, I_D = 500 mA	2N7000	–	1.2	5	Ω
		V_{GS} = 10 V, I_D = 500 mA, T_C = 125°C		–	1.9	9	
		V_{GS} = 4.5 V, I_D = 75 mA		–	1.8	5.3	
		V_{GS} = 10 V, I_D = 500 mA	2N7002	–	1.2	7.5	
		V_{GS} = 10 V, I_D = 500 mA, T_C = 100°C		–	1.7	13.5	
		V_{GS} = 5 V, I_D = 50 mA		–	1.7	7.5	
		V_{GS} = 5 V, I_D = 50 mA, T_C = 100°C		–	2.4	13.5	
		V_{GS} = 10 V, I_D = 500 mA	NDS7002A	–	1.2	2	
		V_{GS} = 10 V, I_D = 500 mA, T_C = 125°C		–	2	3.5	
		V_{GS} = 5 V, I_D = 50 mA		–	1.7	3	
		V_{GS} = 5 V, I_D = 50 mA, T_C = 125°C		–	2.8	5	
$V_{DS(on)}$	Drain−Source On−Voltage	V_{GS} = 10 V, I_D = 500 mA	2N7000	–	0.6	2.5	V
		V_{GS} = 4.5 V, I_D = 75 mA		–	0.14	0.4	
		V_{GS} = 10 V, I_D = 500 mA	2N7002	–	0.6	3.75	
		V_{GS} = 5.0 V, I_D = 50 mA		–	0.09	1.5	
		V_{GS} = 10 V, I_D = 500 mA	NDS7002A	–	0.6	1	
		V_{GS} = 5.0 V, I_D = 50 mA		–	0.09	0.15	
$I_{D(on)}$	On−State Drain Current	V_{GS} = 4.5 V, V_{DS} = 10 V	2N7000	75	600	–	mA
		V_{GS} = 10 V, $V_{DS} \geq 2\ V_{DS(on)}$	2N7002	500	2700	–	
		V_{GS} = 10 V, $V_{DS} \geq 2\ V_{DS(on)}$	NDS7002A	500	2700	–	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 200 mA	2N7000	100	320	–	mS
		$V_{DS} \geq 2\ V_{DS(on)}$, I_D = 200 mA	2N7002	80	320	–	
		$V_{DS} \geq 2\ V_{DS(on)}$, I_D = 200 mA	NDS7002A	80	320	–	
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	All	–	20	50	pF
C_{oss}	Output Capacitance		All	–	11	25	
C_{rss}	Reverse Transfer Capacitance		All	–	4	5	
t_{on}	Turn−On Time	V_{DD} = 15 V, R_L = 25 Ω, I_D = 500 mA, V_{GS} = 10 V, R_{GEN} = 25 Ω	2N7000	–	–	10	ns
		V_{DD} = 30 V, R_L = 150 Ω, I_D = 200 mA, V_{GS} = 10 V, R_{GEN} = 25 Ω	2N7002 NDS7002A	–	–	20	
t_{off}	Turn−Off Time	V_{DD} = 15 V, R_L = 25 Ω, I_D = 500 mA, V_{GS} = 10 V, R_{GEN} = 25 Ω	2N7000	–	–	10	ns
		V_{DD} = 30 V, R_L = 150 Ω, I_D = 200 mA, V_{GS} = 10 V, R_{GEN} = 25 Ω	2N7002 NDS7002A	–	–	20	

ELECTRICAL CHARACTERISTICS (continued)
Values are at T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Type	Min.	Typ.	Max.	Unit
DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
I_S	Maximum Continuous Drain–Source Diode Forward Current		2N7002	–	–	115	mA
			NDS7002A	–	–	280	
I_{SM}	Maximum Pulsed Drain–Source Diode Forward Current		2N7002	–	–	0.8	A
			NDS7002A	–	–	1.5	
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 115 mA (Note 1)	2N7002	–	0.88	1.5	V
		V_{GS} = 0 V, I_S = 400 mA (Note 1)	NDS7002A	–	0.88	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
1. Pulse test: Pulse Width ≤ 300 μs, Duty Cycel ≤ 2 %

TYPICAL PERFORMANCE CHARACTERISTICS

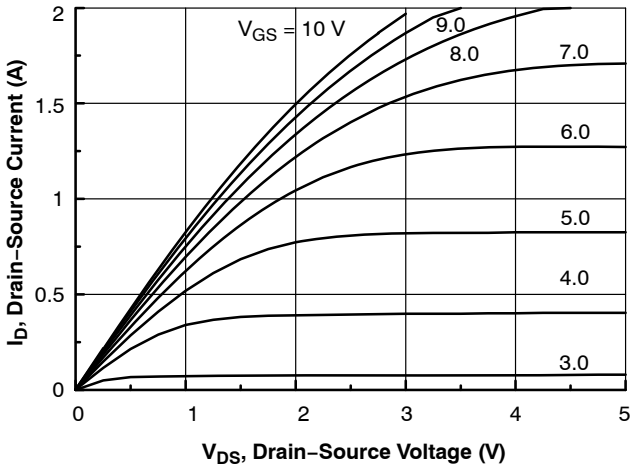


Figure 1. On–Region Characteristics

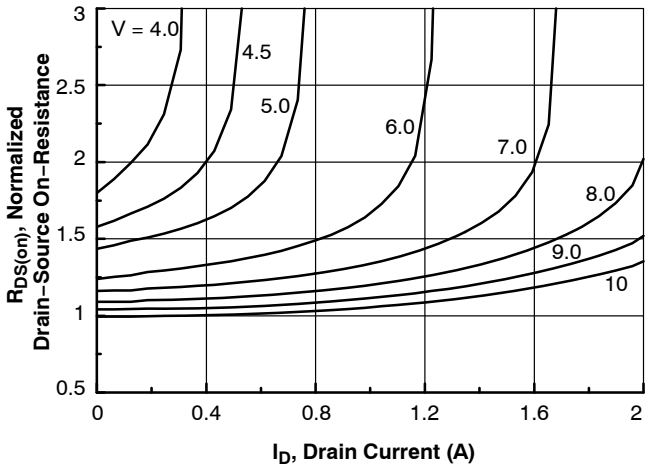


Figure 2. On–Resistance Variation with Gate Voltage and Drain Current

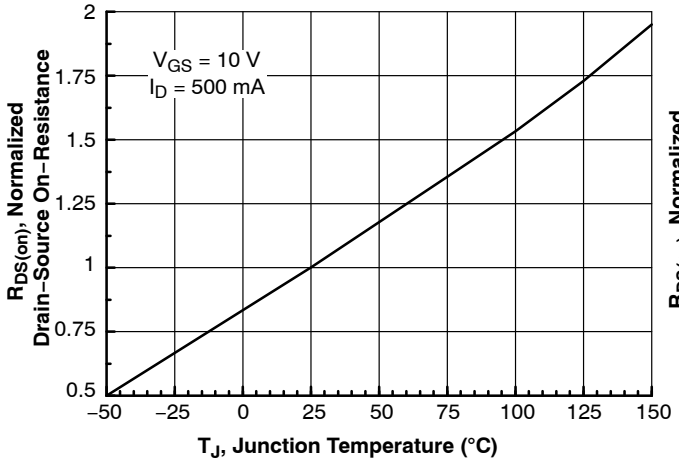


Figure 3. On–Resistance Variation with Temperature

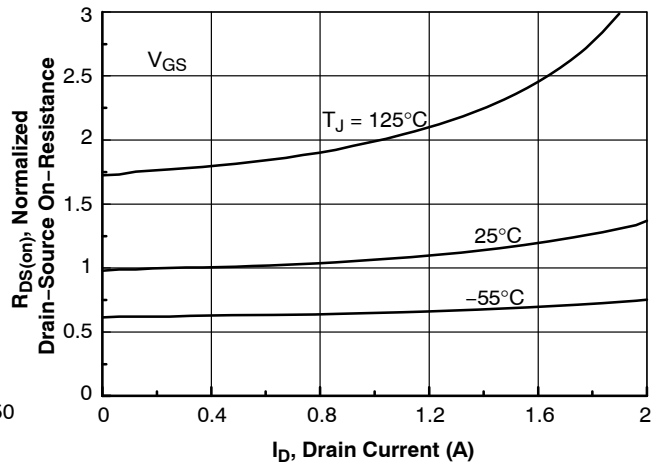


Figure 4. On–Resistance Variation with Drain Current and Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

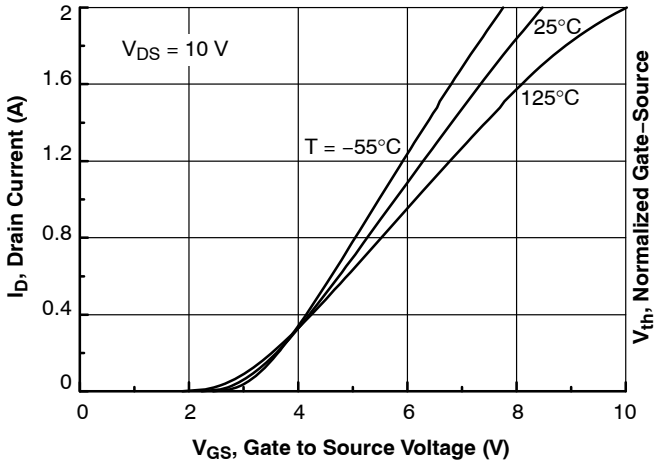


Figure 5. Transfer Characteristics

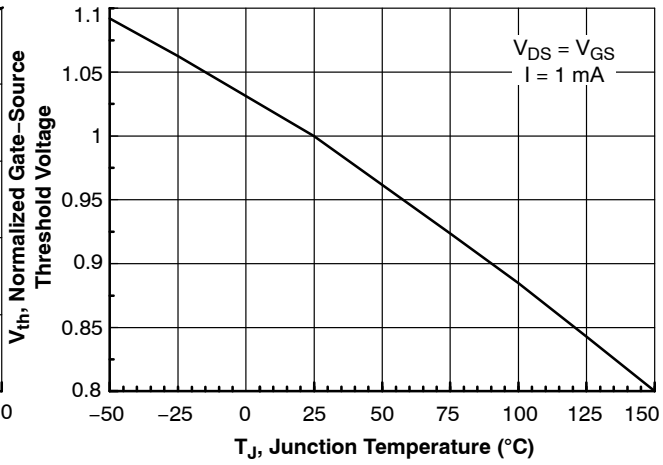


Figure 6. Gate Threshold Variation with Temperature

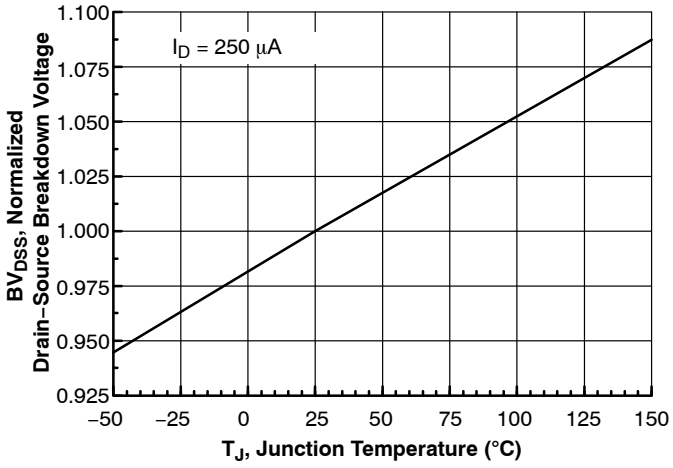


Figure 7. Breakdown Voltage Variation with Temperature

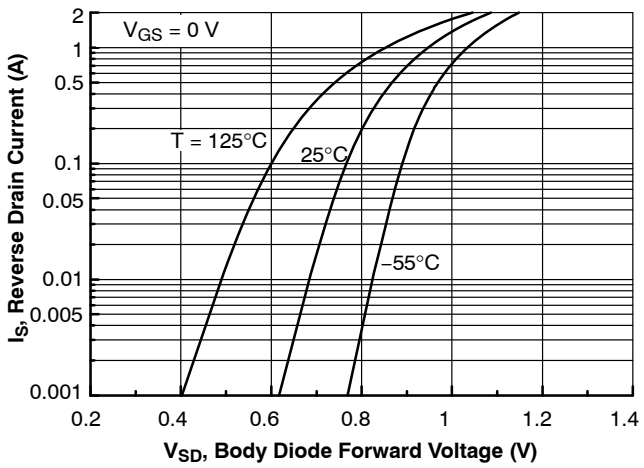


Figure 8. Body Diode Forward Voltage Variation with

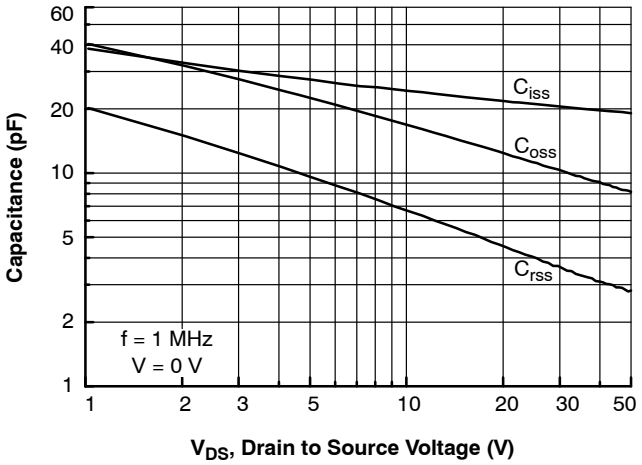


Figure 9. Capacitance Characteristics

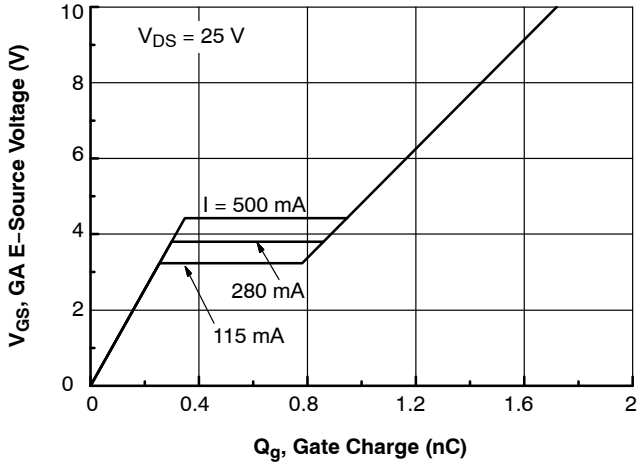


Figure 10. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

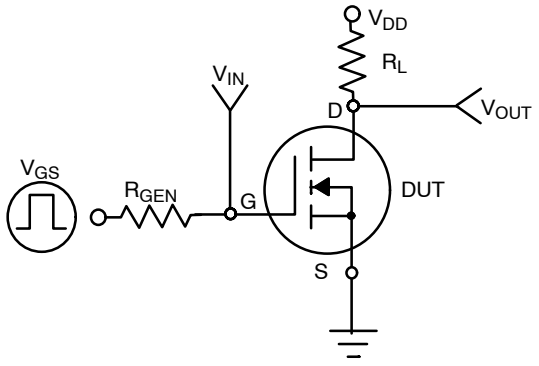


Figure 11. Switching Test Circuit

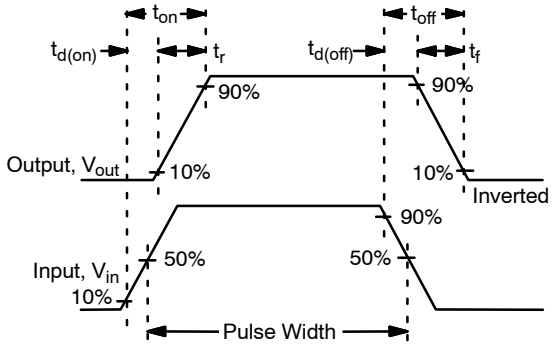


Figure 12. Switching Waveforms

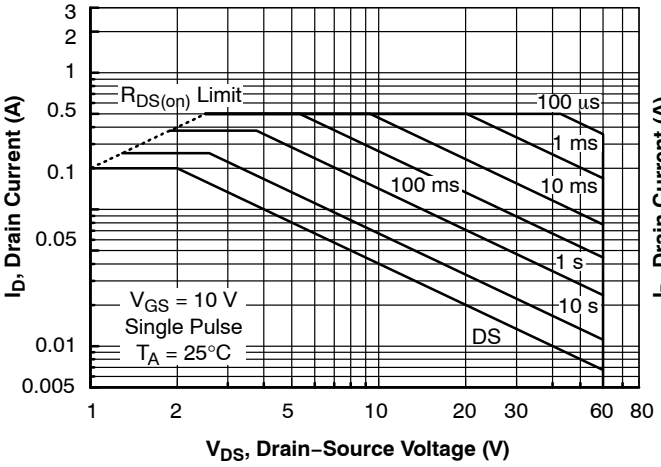


Figure 13. 2N7000 Maximum Safe Operating Area

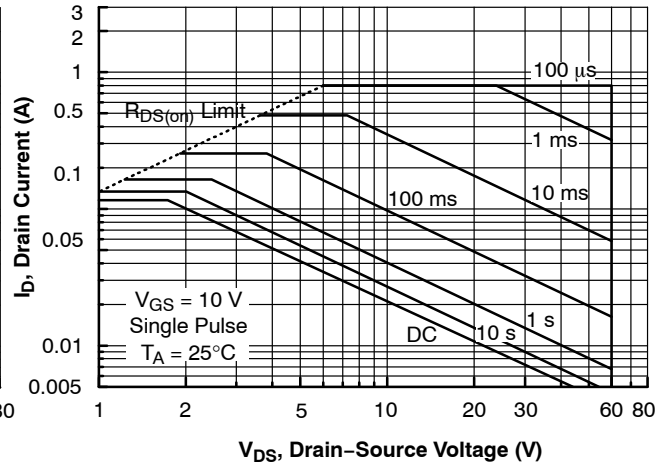


Figure 14. 2N7002 Maximum Safe Operating Area

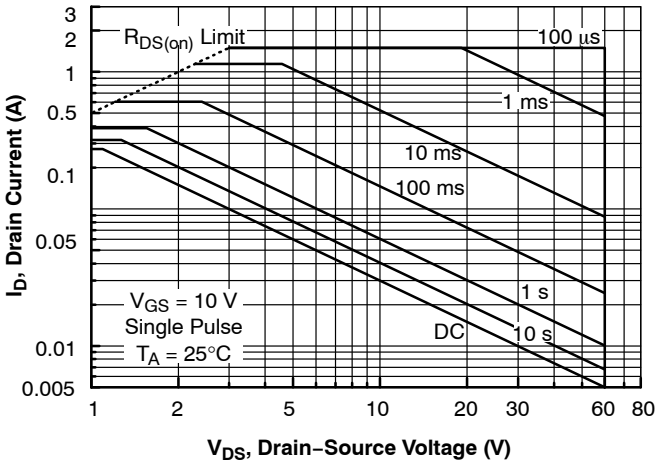


Figure 15. NDS7000A Maximum Safe Operating Area

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

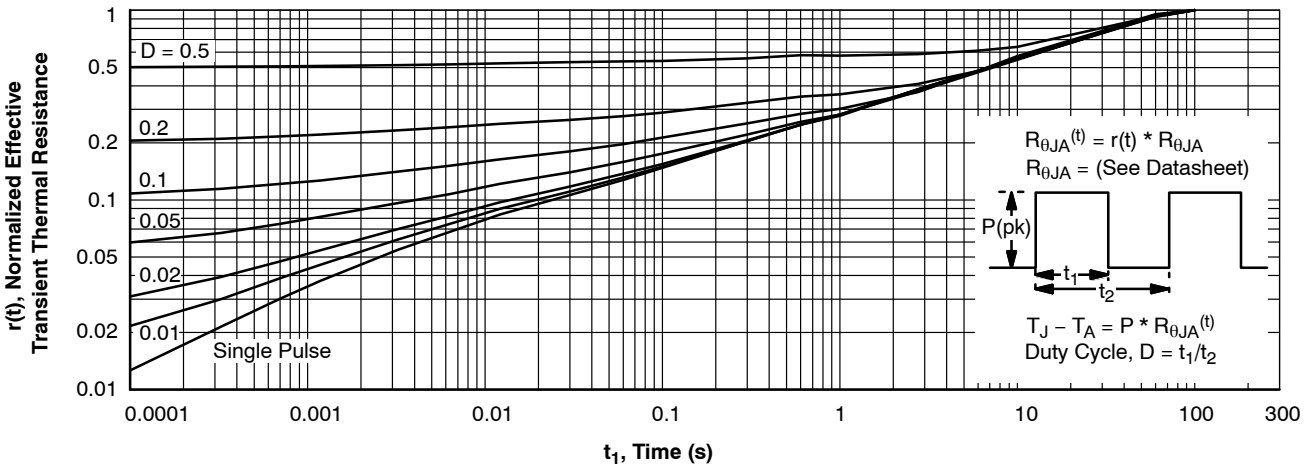


Figure 16. TO−92, 2N7000 Transient Thermal Response Curve

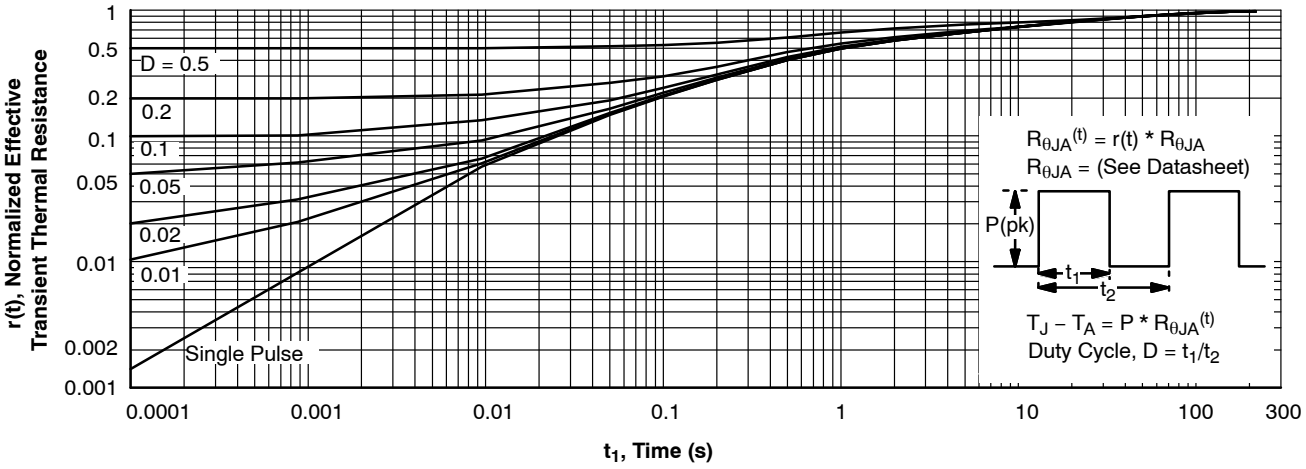


Figure 17. SOT−23, 2N7002 / NDS7002A Transient Thermal Response Curve

ORDERING INFORMATION

Part Number	Marking	Package	Packing Method†	Min Order Qty / Immediate Pack Qty
2N7000	2N7000	TO−92 3L (Pb−Free)	Bulk	10000 / 1000
2N7000−D74Z			Ammo	2000 / 2000
2N7000−D75Z			Tape and Reel	2000 / 2000
2N7000−D26Z				2000 / 2000
2N7002	702	SOT−23 3L (Pb−Free)	Tape and Reel	3000 / 3000
NDS7002A	712			3000 / 3000

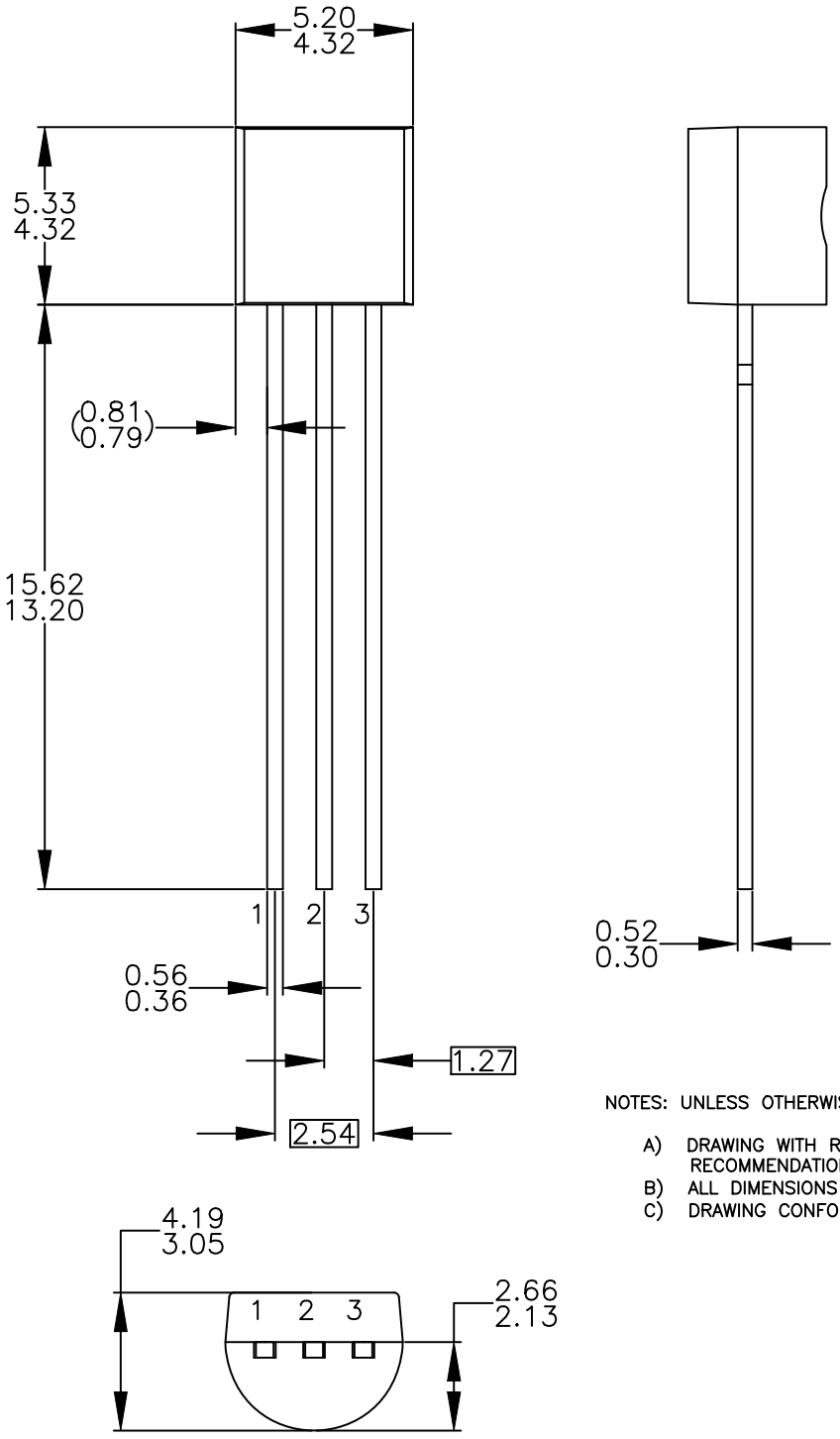
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TO−92 3 4.825x4.76
CASE 135AN
ISSUE O

DATE 31 JUL 2016



NOTES: UNLESS OTHERWISE SPECIFIED

A) DRAWING WITH REFERENCE TO JEDEC TO−92 RECOMMENDATIONS.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M−2009.

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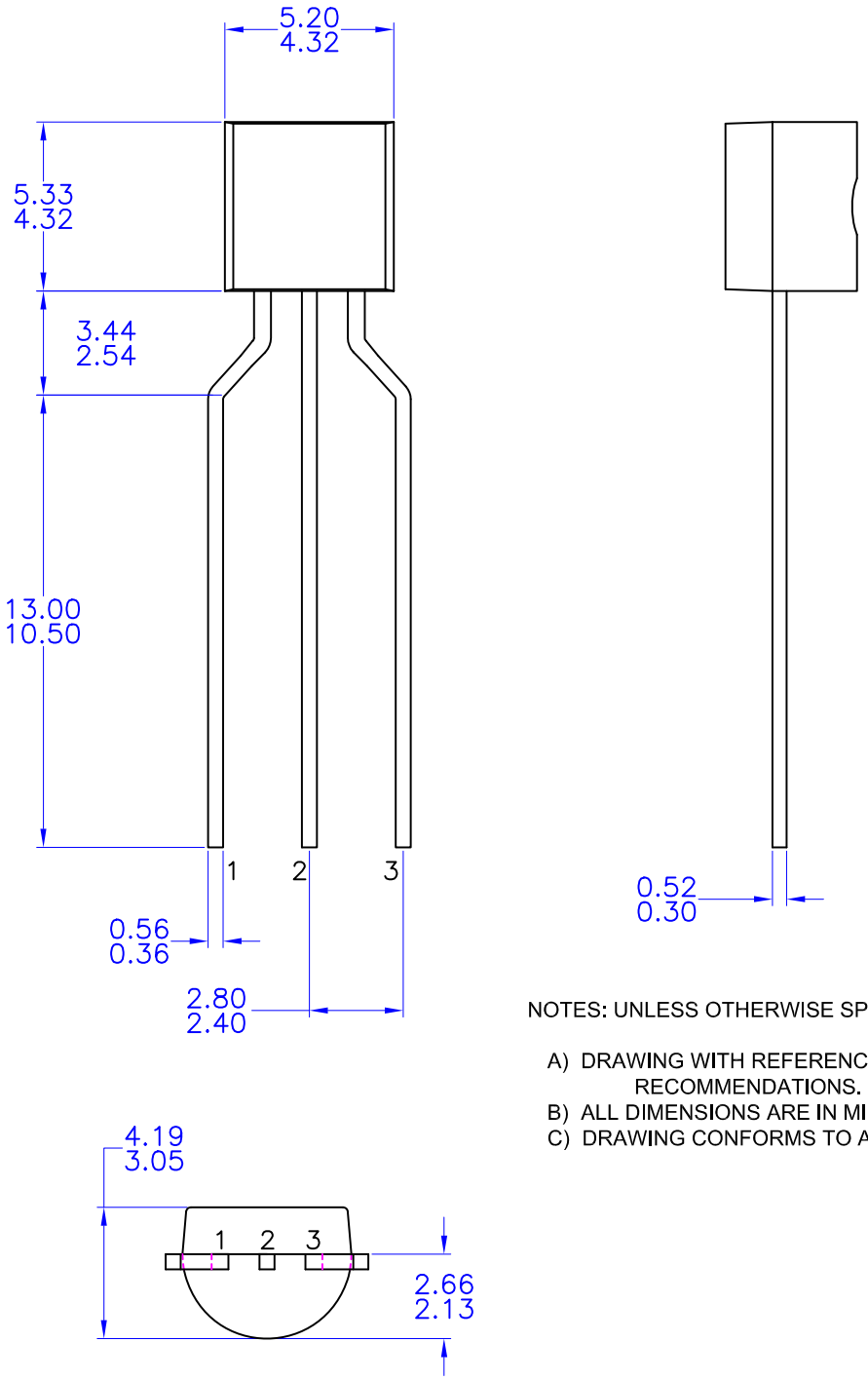
DESCRIPTION:	**TO−92 3 4.825X4.76**	**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TO−92 3 4.83x4.76 LEADFORMED
CASE 135AR
ISSUE O

DATE 30 SEP 2016



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A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M-1994

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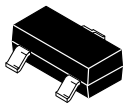
DESCRIPTION:	**TO−92 3 4.83X4.76 LEADFORMED**		**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

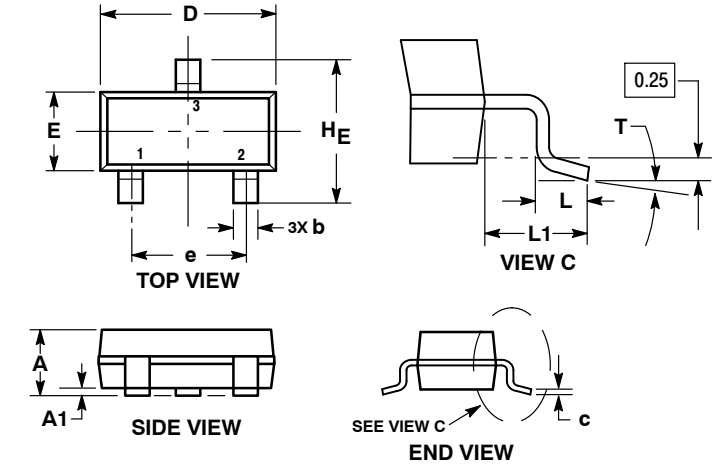
ON Semiconductor®



SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

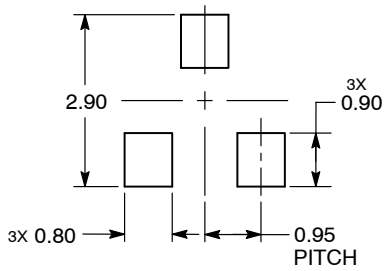
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

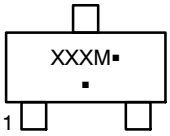
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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